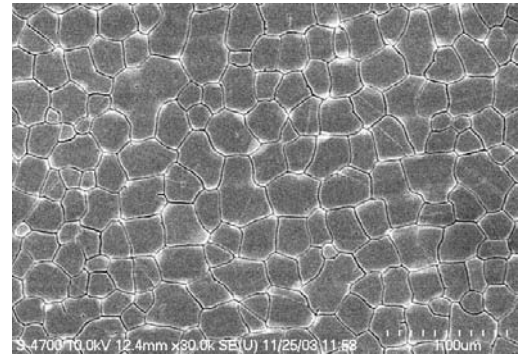
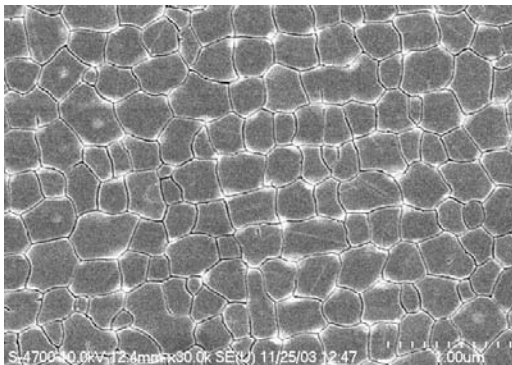


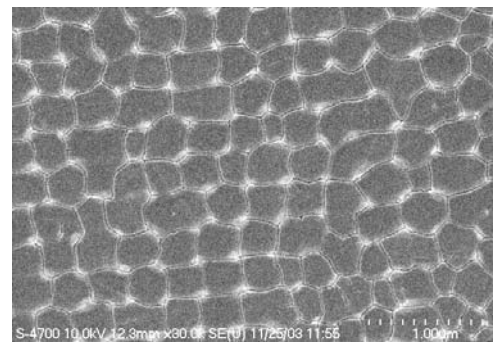
(a)



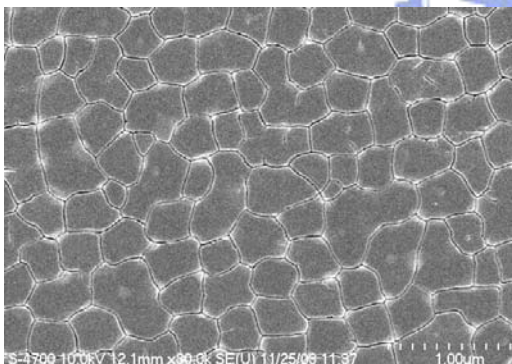
(b)



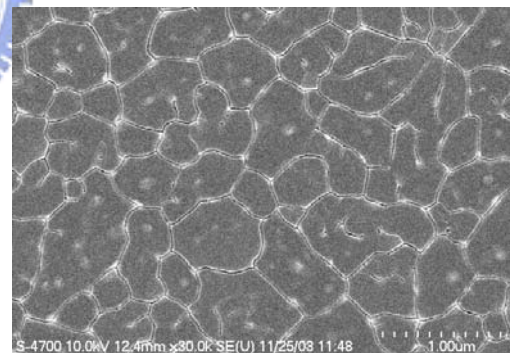
(c)



(d)

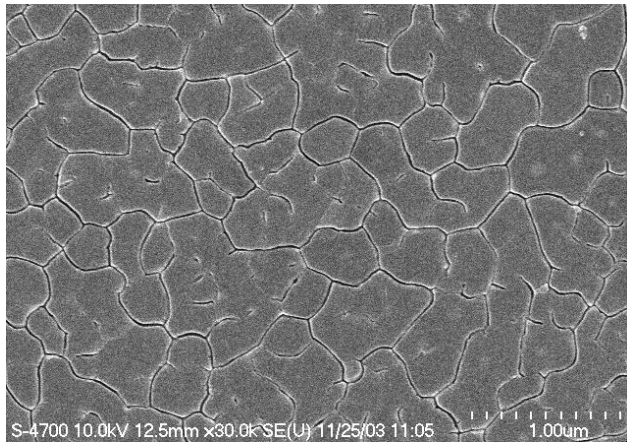


(e)

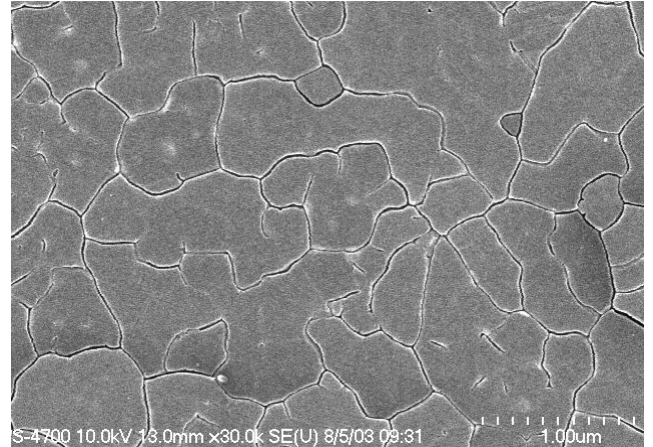


(f)

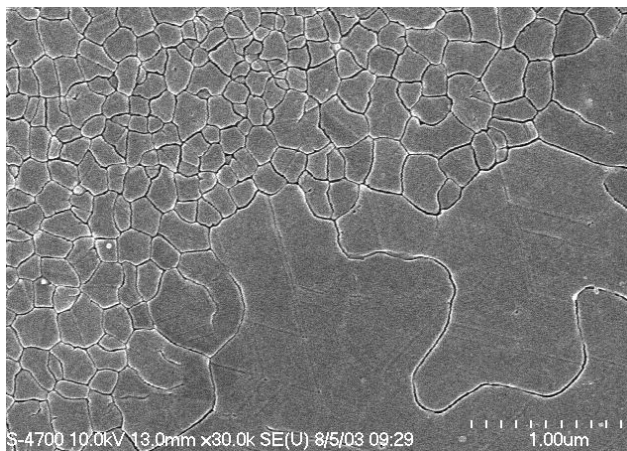
**Fig. 3-30** SEM micrographs of excimer laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The applied laser energy densities are (a) 350, (b) 360, (c) 370, (d) 380 (e) 390 (f) 400  $\text{mJ}/\text{cm}^2$  in the  $\text{O}_2$  ambiance with concentration 5000ppm. The laser energy 950mJ, frequency 300Hz, power 285W, scan speed 6mm/sec, pitch 0.02mm, beam width 0.4mm, pre treatment clean with HF 1% for 30sec



(a)



(b)



(c)

**Fig. 3-31** SEM micrographs of excimer laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The applied laser energy densities are (a) 410, (b) 420, (c) 430  $\text{mJ}/\text{cm}^2$  in the  $\text{O}_2$  ambience with concentration 5000ppm. The laser energy 950mJ, frequency 300Hz, power 285W, scan speed 6mm/sec, pitch 0.02mm, beam width 0.4mm, pre treatment clean with HF 1% for 30sec.